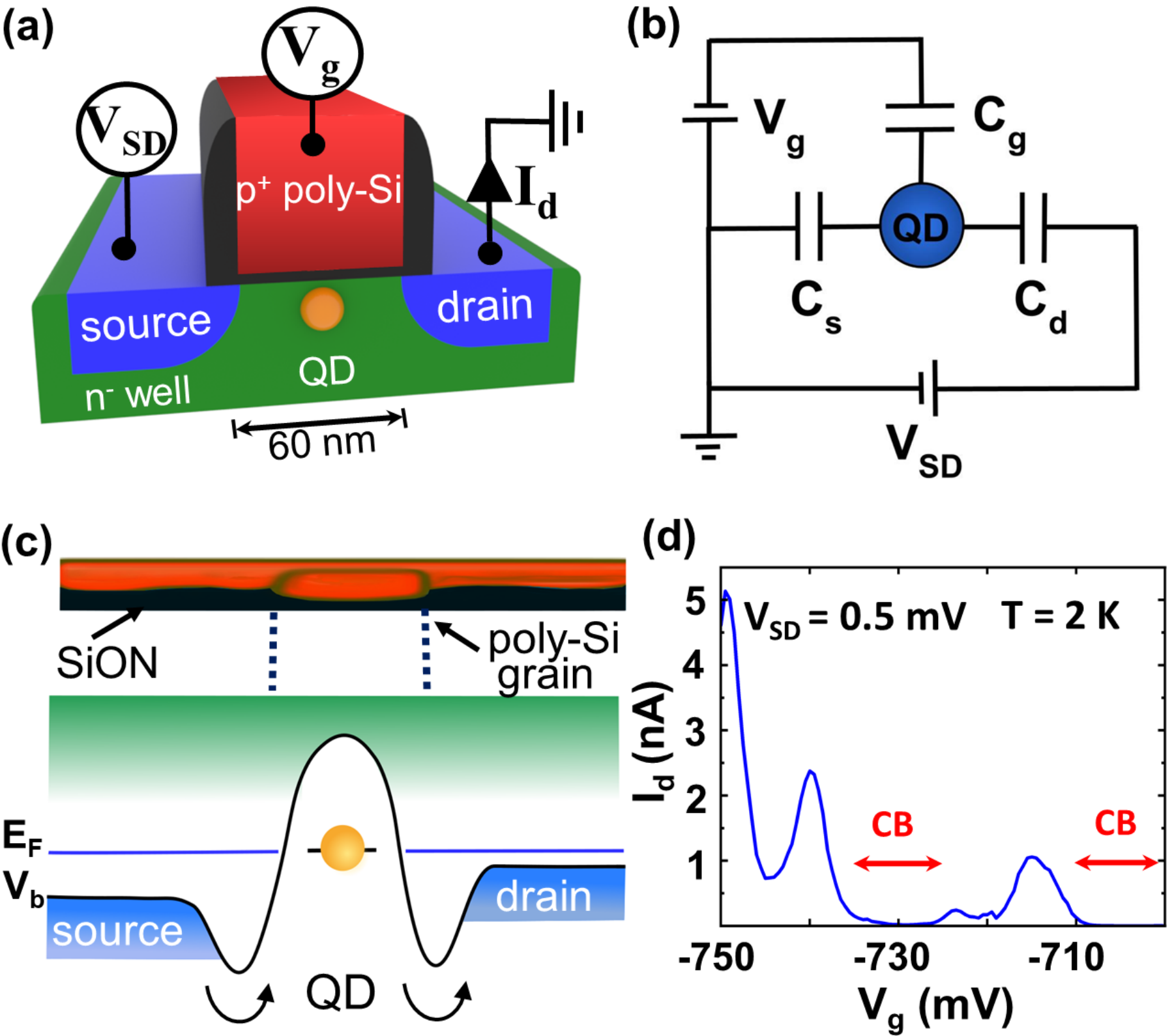
(a)
V_g
V_{SD}
p^+ poly-Si
I_d
source
drain
QD
n^- well
60 nm
(b)
V_g
C_g
QD
C_s
C_d
V_{SD}
(c)
SiON
poly-Si grain
E_F
V_b
source
drain
QD
(d)
V_{SD} = 0.5 mV T = 2 K
I_d (nA)
CB
CB
-750
-730
-710
V_g (mV)